



**ZXTP25012EZ** 

### 20V PNP HIGH GAIN TRANSISTOR IN SOT89

### Features

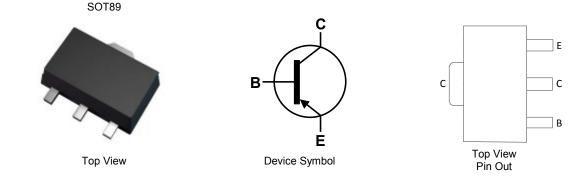
- BV<sub>CEO</sub> > -12V
- I<sub>C</sub> = -4.5A High Continuous Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -70mV @ -1A</li>
- $R_{sat} = 45m\Omega$  for a Low Equivalent On-Resistance
- P<sub>D</sub> = 2.4W Power Dissipation
- Complementary part number ZXTN25012EZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### Application

- High side switch
- Battery charging
- Regulator circuits
- Buck converters
- MOSFET gate drivers

## **Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.05 grams (Approximate)



### Ordering Information (Note 4)

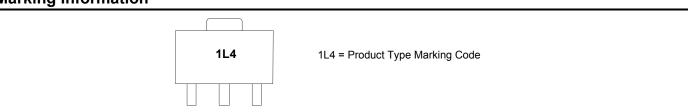
Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTP25012EZTA	Standard	1L4	7	12	1,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**





## Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-12	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ι <sub>C</sub>	-4.5	A
Peak Pulse Collector Current (Single Pulse)	Ісм	-10	A
Base Current	IB	-1	A

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	1.8 14.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	PD	2.4 19.2	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	PD	4.46 35.7	W mW/°C
Power Dissipation (Note 9) Linear Derating Factor	PD	19.2 153	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R <sub>θJA</sub>	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	R <sub>eJC</sub>	7.95	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

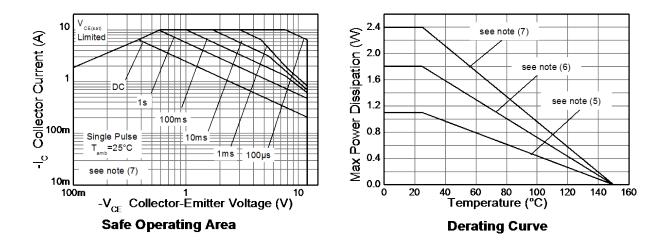
Notes: 5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.

6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.

Same as note (5), except the device is measured at t<5 seconds.</li>
Junction to case (collector tab). Typical.

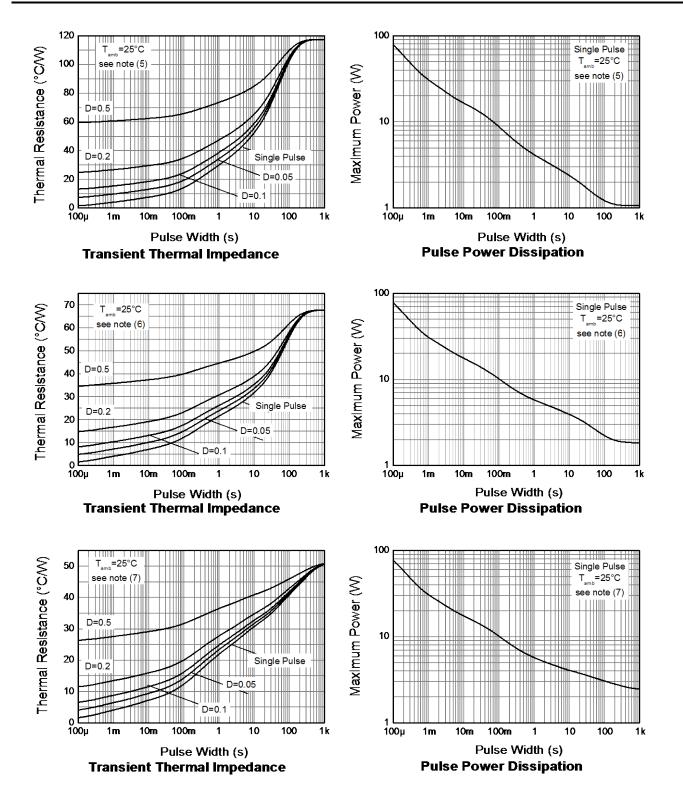


# Thermal Characteristics and Derating Information





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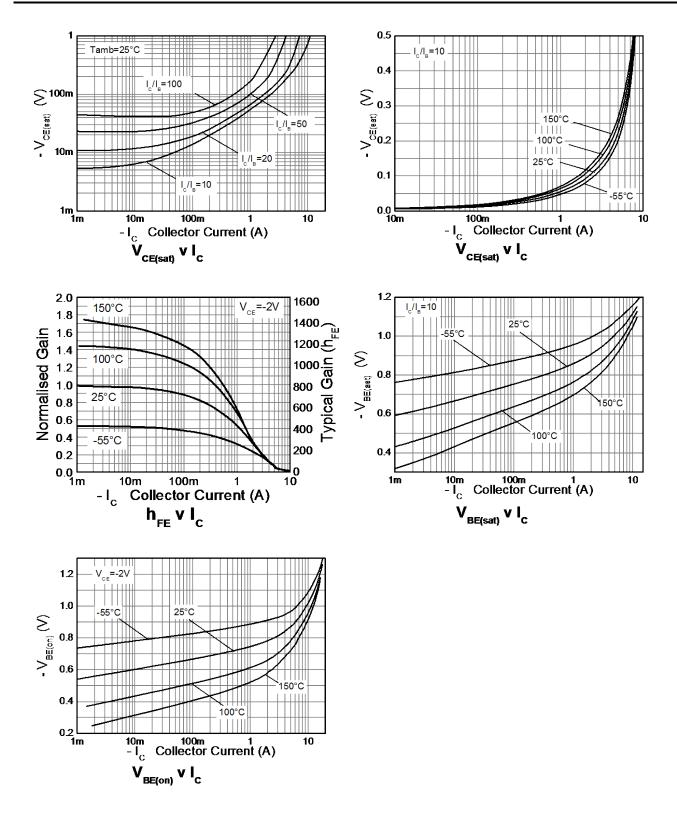
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

		•	-			
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-12	-35	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-12	-25	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.5	_	V	I <sub>E</sub> = -100μA
Collector Cut-Off Current	I <sub>CBO</sub>	_	-1	-50 -0.5	nA μA	V <sub>CB</sub> = -12V V <sub>CB</sub> = -12V, T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	_	-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	_	-55 -155 -185 -200	-70 -265 -355 -285	mV	$I_{C} = -1A, I_{B} = -100mA$ $I_{C} = -1A, I_{B} = -10mA$ $I_{C} = -2A, I_{B} = -40mA$ $I_{C} = -5A, I_{B} = -450mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	—	-990	-1100	mV	I <sub>C</sub> = -4.5A, I <sub>B</sub> = -450mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	—	-865	-975	mV	$I_{C}$ = -4.5A, $V_{CE}$ = -2V
Static forward current transfer ratio (Note 10)	hfe	500 300 40 —	800 450 85 15	1500 — — —	_	$I_{C} = -10 \text{mA}, V_{CE} = -2V$ $I_{C} = -1A, V_{CE} = -2V$ $I_{C} = -4.5A, V_{CE} = -2V$ $I_{C} = -10A, V_{CE} = -2V$
Transitional frequency	f <sub>T</sub>	—	310	_	MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V, f = 100MHz
Input Capacitance	Ci <sub>bo</sub>	_	127	250	pF	V <sub>EB</sub> = -0.5V, f = 1MHz
Output Capacitance	C <sub>obo</sub>	_	16.9	30	pF	V <sub>CB</sub> = -10V, f = 1MHz
Delay time	t <sub>d</sub>	_	41	—	ns	
Rise time	tr	—	62	—	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -1A,
Storage time	ts	—	179	_	ns	I <sub>B1</sub> = -I <sub>B2</sub> = -10mA
Fall time	t <sub>f</sub>	_	65	_	ns	7

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



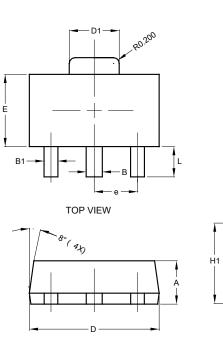
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

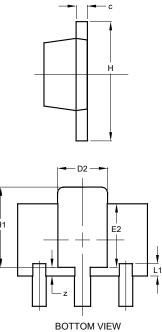




# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT89

SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
z	0.20	0.40	0.30		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

	-	
Dimensions	Value	
	(in mm)	
С	1.500	
G	0.244	
X	0.580	
X1	0.760	
X2	1.933	
Y	1.730	
Y1	3.030	
Y2	1.500	
Y3	0.770	
Y4	4.530	

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